

### **REMARKS**

Claims 1, 3-5, and 7-22 are pending in the above-identified application. Claims 1, 3-5, and 7-22 were rejected. With this amendment, claims 1, 15 and 19 were amended and claim 23 was added. Applicant maintains that no new matter has been added. Accordingly, claims 1, 3-5, and 7-23 are at issue in the above-identified application.

Applicant would like to thank Examiner Anderson for his courteous and helpful interview held with Applicant's representative on June 14, 2005. During the interview, proposed amendments to claim 1 were discussed.

### **35 U.S.C. § 103 Obviousness Rejection of Claims**

Claims 1, 3-5 and 7-22 were rejected under 35 U.S.C. §103(a) as being unpatentable over *Kiyoku et al.* (U.S. Patent No. 6,153,010) in view of *Sugiura et al.* (U.S. Patent No. 6,015,979). Applicant respectfully traverse this rejection.

Amended claim 1, from which claims 3-5 and 7-14 depend, recites a method of manufacturing a crystal of a III-V compound of the nitride system comprising removing the second mask pattern to expose the second crystal layer and growing a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer. In contrast, neither *Kiyoku et al.* nor *Sugiura et al.*, either alone or in combination, teach or suggest removing the second mask pattern to expose the second crystal layer and growing a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer. For example, *Kiyoku et al.* teaches forming a nitride semiconductor layer 71 on a support member 10, forming recess portions 72a to 72f in the nitride semiconductor layer 71, and *then* forming growth control masks 73a to 73g and 74a to 74f on the nitride semiconductor layer 71. (See *Kiyoku et al.*, col. 15, lines 4-44, and FIGS. 7A-7D.) *Kiyoku et al.* does not teach or even

suggest etching the semiconductor layer 71 through the growth control masks 73a to 73g and 74a to 74f.

Accordingly, Applicant submits that the claimed invention is not anticipated by nor obvious over the applied references, either alone or in combination. Withdrawal of these grounds of rejection is respectfully requested.

In view of the foregoing, Applicant submits that the application is in condition for allowance. Notice to that effect is requested.

Respectfully submitted,

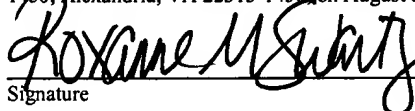
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